

International  
**IR** Rectifier

**AUTOMOTIVE MOSFET**

**IRFBA1405P**

**Typical Applications**

- Electric Power Steering (EPS)
- Anti-lock Braking System (ABS)
- Wiper Control
- Climate Control
- Power Door

**Benefits**

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax

**Description**

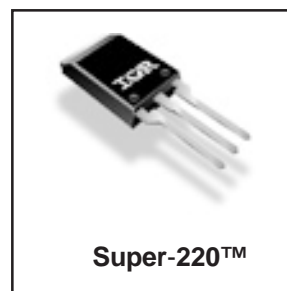
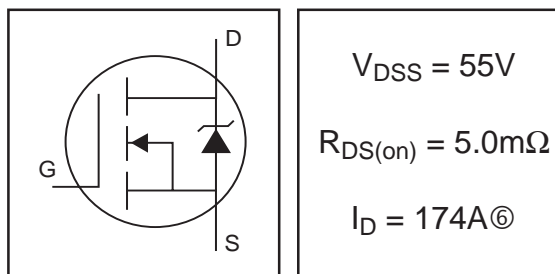
Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this MOSFET are a 175°C junction operating temperature, fast switching speed and improved ruggedness in single and repetitive avalanche. The Super-220™ is a package that has been designed to have the same mechanical outline and pinout as the industry standard TO-220 but can house a considerably larger silicon die. The result is significantly increased current handling capability over both the TO-220 and the much larger TO-247 package. The combination of extremely low on-resistance silicon and the Super-220™ package makes it ideal to reduce the component count in multiparalleled TO-220 applications, reduce system power dissipation, upgrade existing designs or have TO-247 performance in a TO-220 outline. This package has been designed to meet automotive, Q101, qualification standard.

These benefits make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

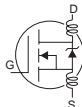
**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	174 <sup>⑥</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	123 <sup>⑥</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	680	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	330	W
	Linear Derating Factor	2.2	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>②</sup>	560	mJ
I <sub>AR</sub>	Avalanche Current	See Fig.12a, 12b, 15, 16	A
E <sub>AR</sub>	Repetitive Avalanche Energy <sup>⑦</sup>		mJ
dv/dt	Peak Diode Recovery dv/dt <sup>③</sup>	5.0	V/ns
T <sub>J</sub>	Operating Junction and	-40 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to + 175	
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Recommended clip force	20	N

HEXFET® Power MOSFET



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

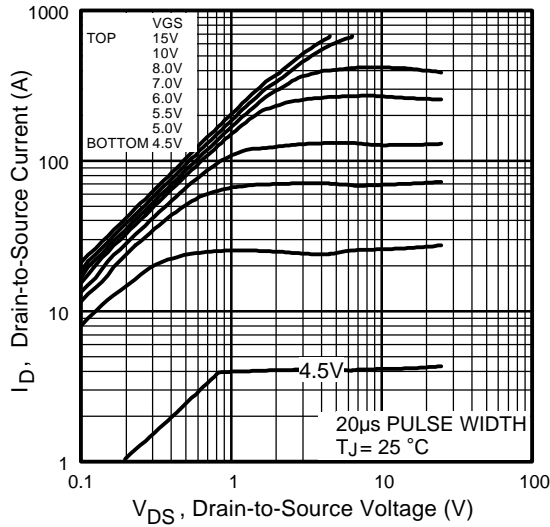
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	4.3	5.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 101A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	69	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 110A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	170	260	nC	I <sub>D</sub> = 101A
Q <sub>gs</sub>	Gate-to-Source Charge	—	44	66		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	62	93		V <sub>GS</sub> = 10V ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	—	ns	V <sub>DD</sub> = 38V
t <sub>r</sub>	Rise Time	—	190	—		I <sub>D</sub> = 110A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	130	—		R <sub>G</sub> = 1.1Ω
t <sub>f</sub>	Fall Time	—	110	—		V <sub>GS</sub> = 10V ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	5480	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	1210	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	280	—		f = 1.0MHz, See Fig. 5
C <sub>oss</sub>	Output Capacitance	—	5210	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	900	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 44V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance ⑤	—	1500	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 44V

## Source-Drain Ratings and Characteristics

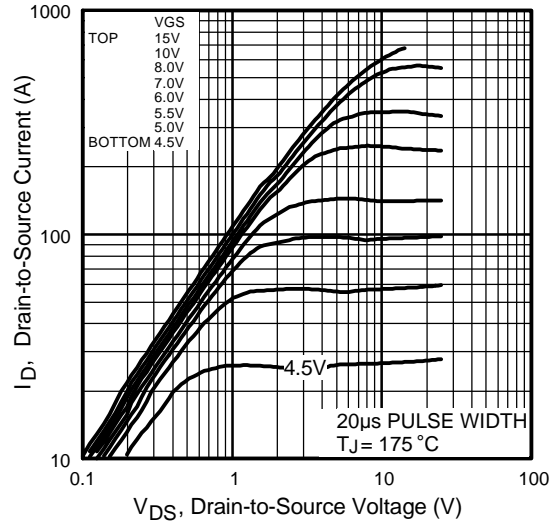
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	174⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	680		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 101A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	88	130	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 101A
Q <sub>rr</sub>	Reverse Recovery Charge	—	250	380	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

## Thermal Resistance

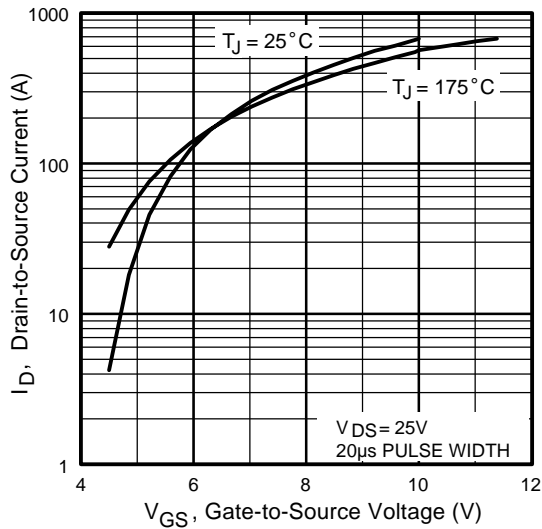
	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	0.45	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient	—	58	



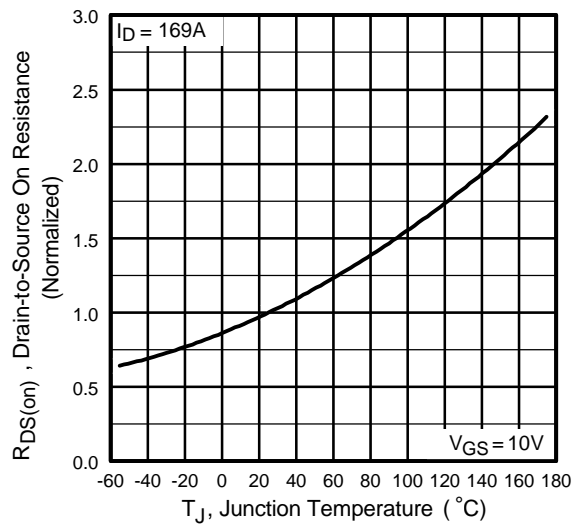
**Fig 1.** Typical Output Characteristics



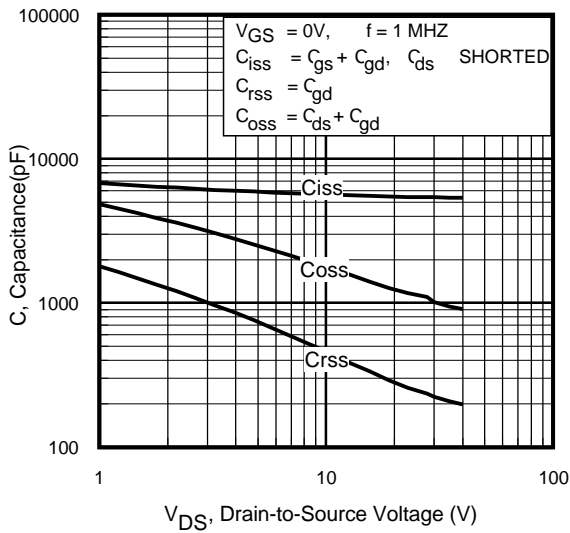
**Fig 2.** Typical Output Characteristics



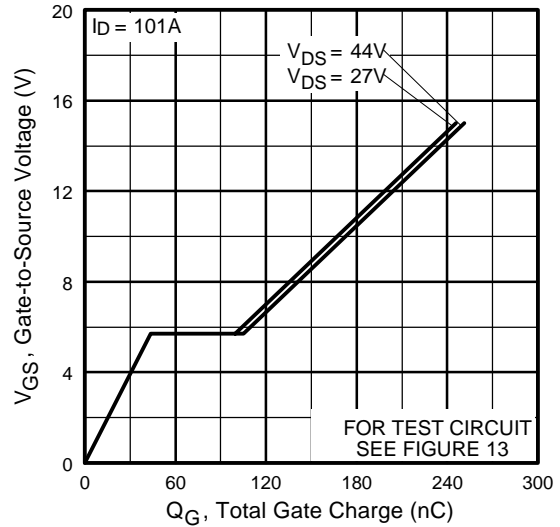
**Fig 3.** Typical Transfer Characteristics



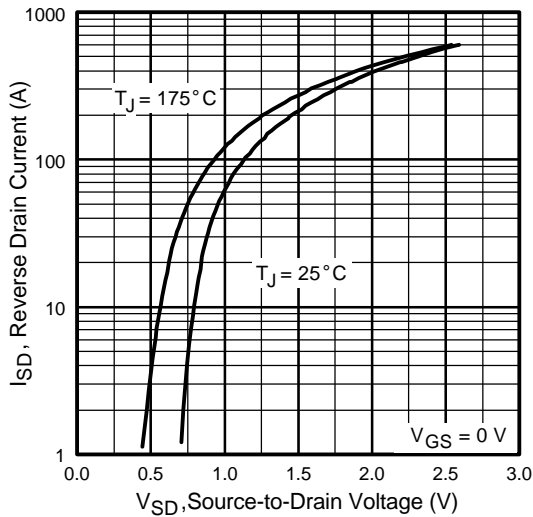
**Fig 4.** Normalized On-Resistance Vs. Temperature



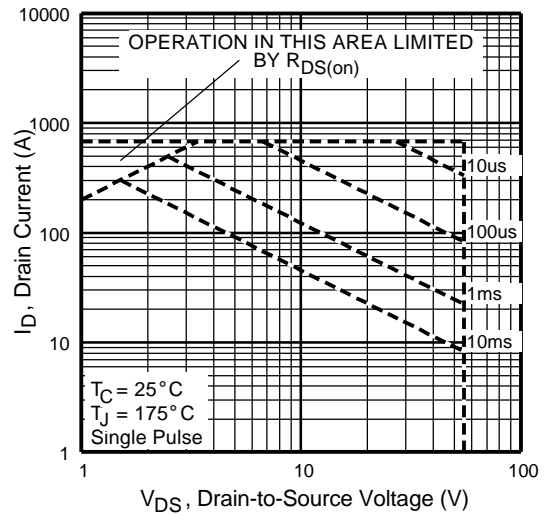
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



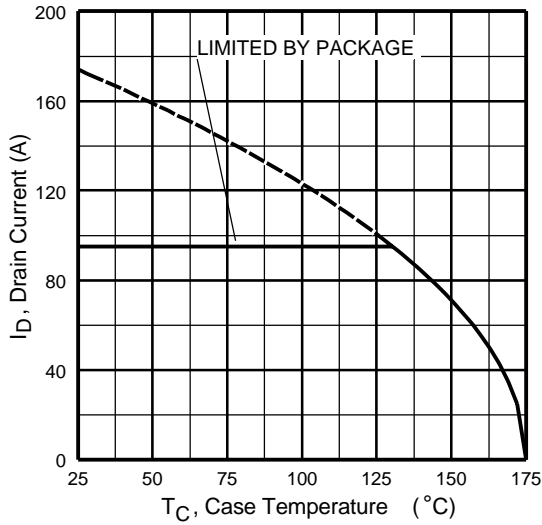
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



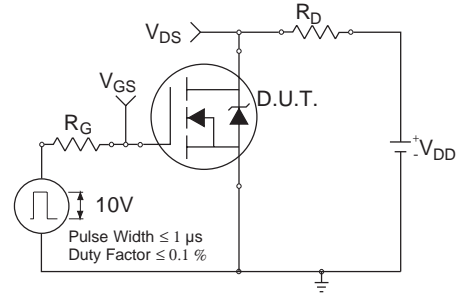
**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area



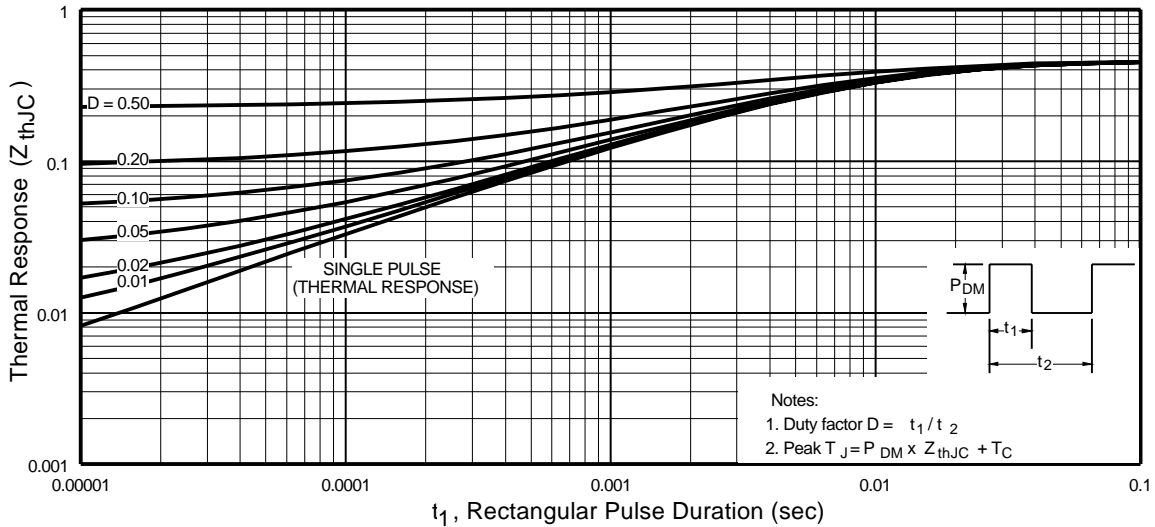
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



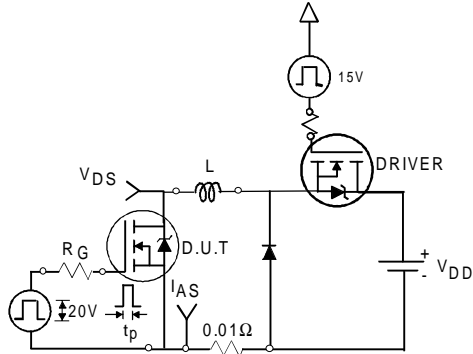
**Fig 10b.** Switching Time Waveforms



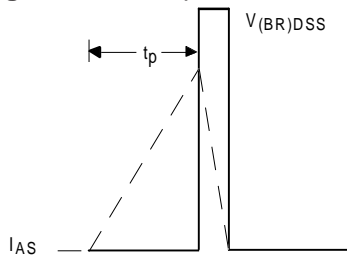
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFBA1405P

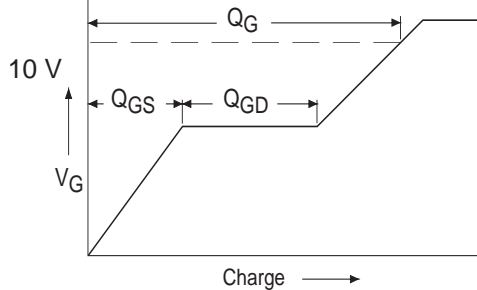
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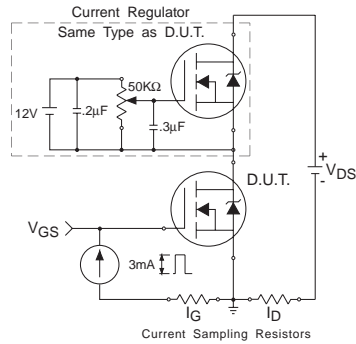
**Fig 12a.** Unclamped Inductive Test Circuit



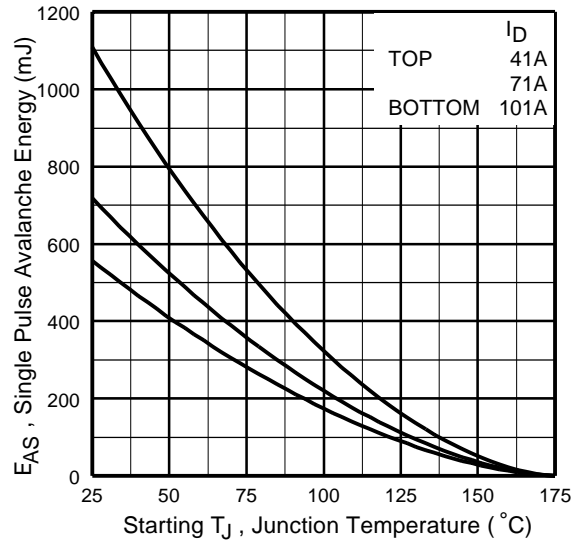
**Fig 12b.** Unclamped Inductive Waveforms



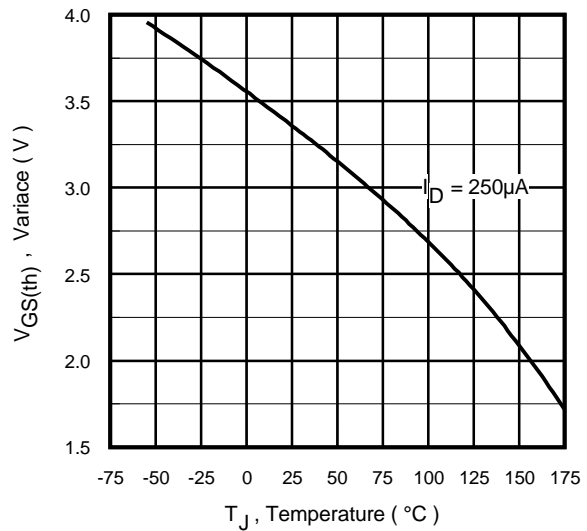
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Threshold Voltage Vs. Temperature

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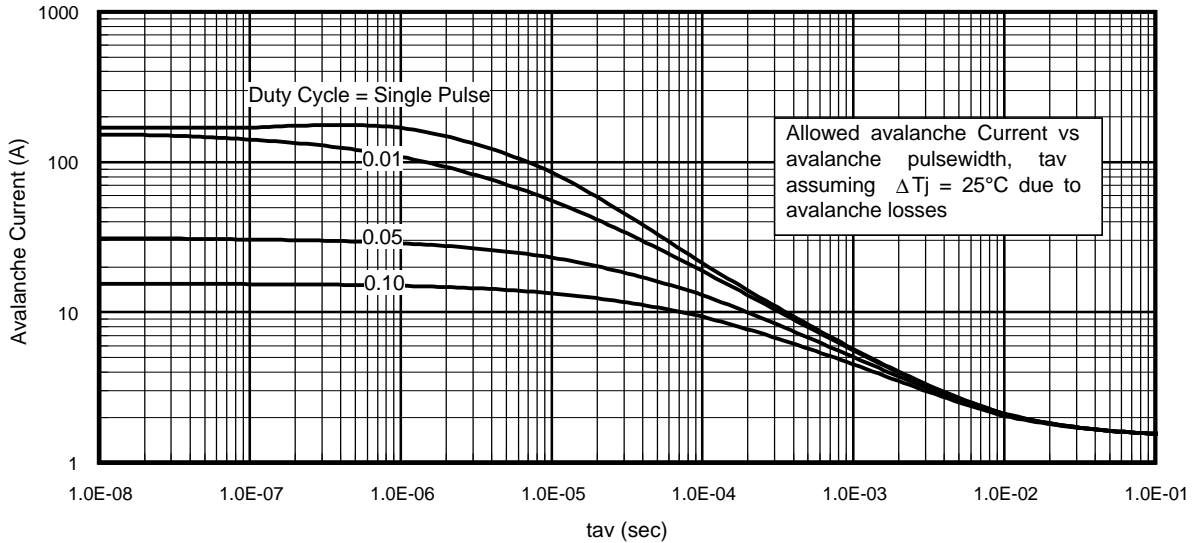


Fig 15. Typical Avalanche Current Vs.Pulsewidth

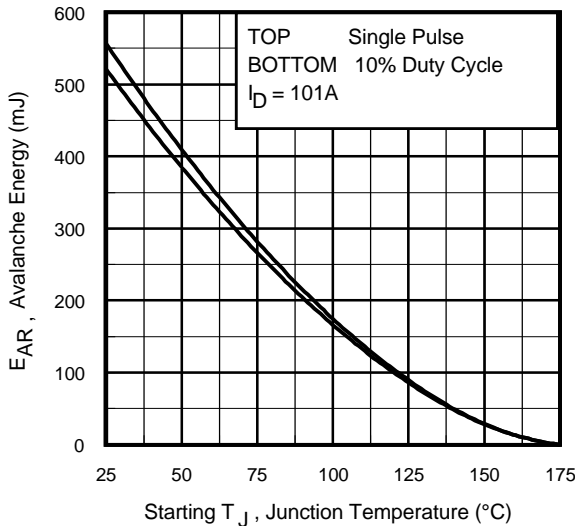


Fig 16. Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at www.irf.com)**

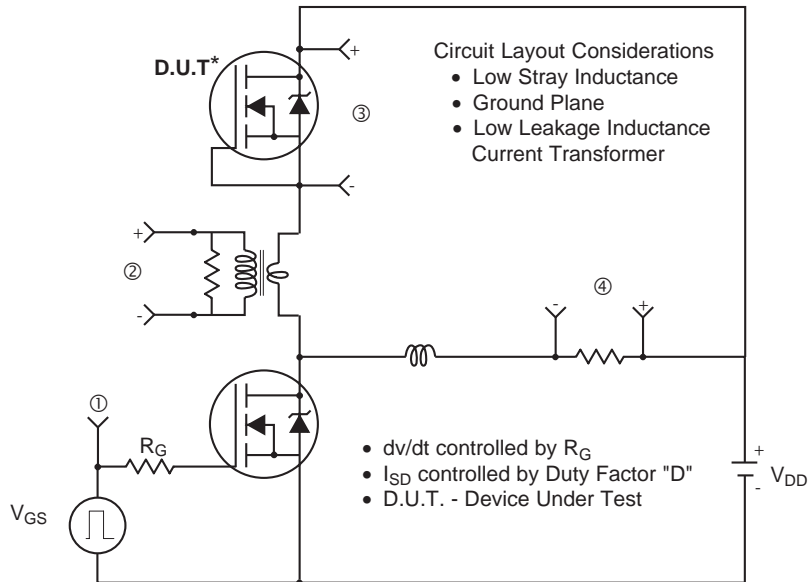
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

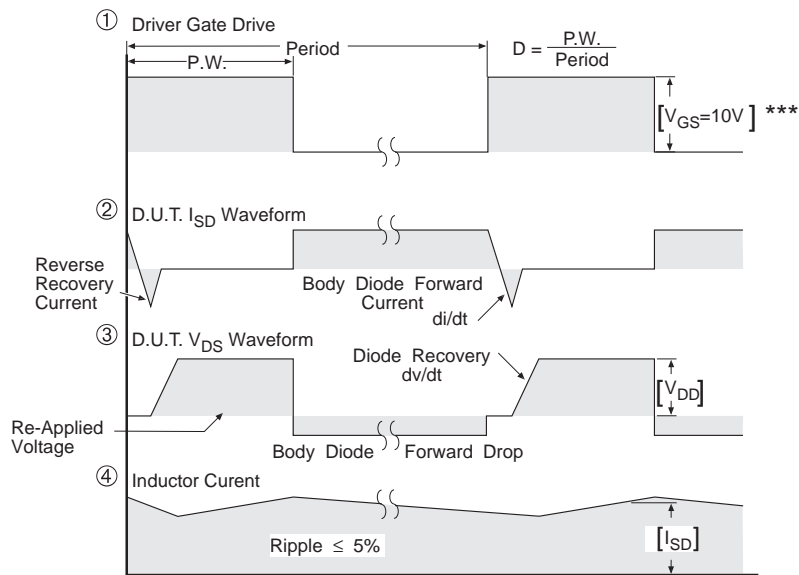
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



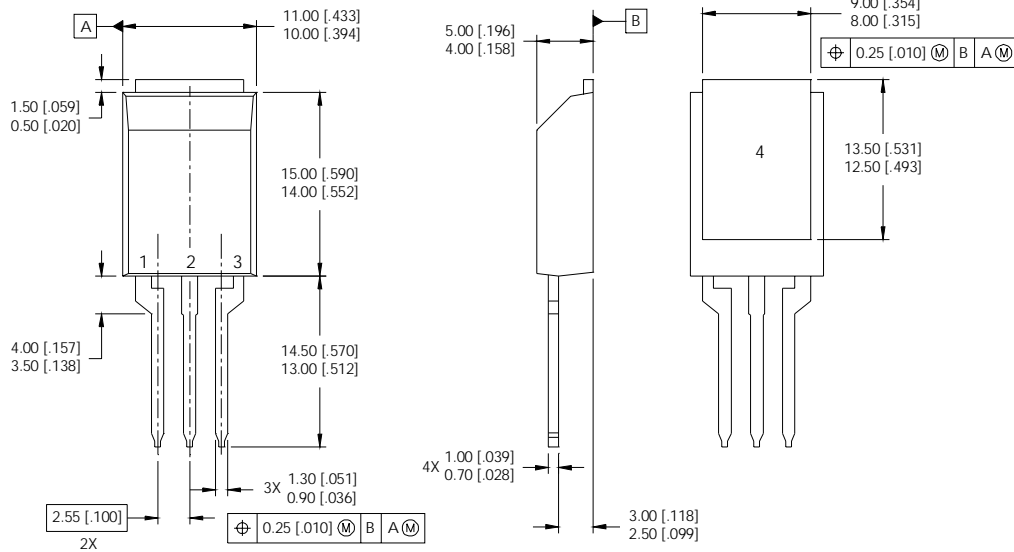
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 17.** For N-channel HEXFET® power MOSFETs



## Super-220™ Package Outline

# IRFBA1405P



### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

### LEAD ASSIGNMENTS

MOSFET	IGBT
1 - GATE	1 - GATE
2 - DRAIN	2 - COLLECTOR
3 - SOURCE	3 - EMITTER
4 - DRAIN	4 - COLLECTOR

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.11\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 101\text{A}$ . (See Figure 12).
- ③  $I_{SD} \leq 101\text{A}$ ,  $di/dt \leq 210\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 40\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ . Refer to AN-1001
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 95A.
- ⑦ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.

Data and specifications subject to change without notice.

This product has been designed and qualified for the automotive [Q101] market.

Qualification Standards can be found on IR's Web site.

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